







CD74HC126, CD54HC126

SCHS144D - NOVEMBER 1998 - REVISED JUNE 2021

CDx4HC126 Quadruple Buffers with 3-State Outputs

1 Features

- **Buffered inputs**
- Wide operating voltage range: 2 V to 6 V
- Wide operating temperature range: -55°C to +125°C
- Supports fanout up to 10 LSTTL loads
- Significant power reduction compared to LSTTL logic ICs

2 Applications

Enable digital signals

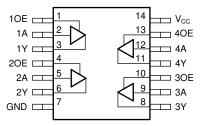
3 Description

This device contains four independent buffers with 3-state outputs. Each gate performs the Boolean function Y = A in positive logic.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
CD74HC126M	SOIC (14)	8.70 mm × 3.90 mm
CD74HC126E	PDIP (14)	19.30 mm × 6.40 mm
CD54HC126F	CDIP (14)	21.30 mm × 7.60 mm

For all available packages, see the orderable addendum at the end of the data sheet.



Functional pinout



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4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

С	Changes from Revision C (September 2003) to Revision D (June 2021)					
•	Updated to new data sheet standards	1				
•	Moved the HCT devices to a standalone data sheet (SCHS416)	1				
•	R _{0,JA} increased for the D package from 86 to 133.6°C/W and decreased for the N package from 80 to					
	62.2°C/W	5				



5 Pin Configuration and Functions

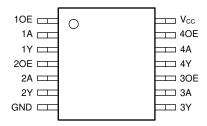


Figure 5-1. D, N, or J Package 14-Pin SOIC, PDIP, or CDIP Top View

Pin Functions

PIN		1/0	DESCRIPTION	
NAME	NO.	_ I/O	DESCRIPTION	
10E	1	Input	Channel 1, Output Enable	
1A	2	Input	Channel 1, Input A	
1Y	3	Output	Channel 1, Output Y	
20E	4	Input	Channel 2, Output Enable	
2A	5	Input	Channel 2, Input A	
2Y	6	Output	Channel 2, Output Y	
GND	7	_	Ground	
3Y	8	Output	Channel 3, Output Y	
3A	9	Input	Channel 3, Input A	
3OE	10	Input	Channel 3, Output Enable	
4Y	11	Output	Channel 4, Output Y	
4A	12	Input	Channel 4, Input A	
40E	13	Input	Channel 4, Output Enable	
V _{CC}	14	_	Positive Supply	



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_1 < -0.5 \text{ V or } V_1 > V_{CC} + 0.5 \text{ V}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	V_O < -0.5 V or V_O > V_{CC} + 0.5 V		±20	mA
Io	Continuous output current	$V_{\rm O}$ > -0.5 V or $V_{\rm O}$ < $V_{\rm CC}$ + 0.5 V		±35	mA
	Continuous current through V _{CC} or GND			±70	mA
TJ	Junction temperature ⁽³⁾			150	°C
	Lead temperature (Soldering 10s)	SOIC - Lead tips only		300	°C
T _{stg}	Storage temperature	-65	150	°C	

⁽¹⁾ Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

6.2 ESD Ratings

			VALUE	UNIT
V	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD)	Electrostatic discharge	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	-	V

⁽¹⁾ JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

1			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		2		6	V
		V _{CC} = 2 V	1.5			
V_{IH}	High-level input voltage	V _{CC} = 4.5 V	3.15			V
		V _{CC} = 6 V	4.2			
		V _{CC} = 2 V			0.5	
V_{IL}	Low-level input voltage	V _{CC} = 4.5 V			1.35	V
		V _{CC} = 6 V			1.8	
VI	Input voltage	·	0		V _{CC}	V
Vo	Output voltage		0		V _{CC}	V
		V _{CC} = 2 V			1000	
t _t	Input transition time	V _{CC} = 4.5 V			500	ns
		V _{CC} = 6 V			400	
T _A	Operating free-air temperature		-55		125	°C

⁽²⁾ The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

⁽³⁾ Guaranteed by design.

²⁾ JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



6.4 Thermal Information

		CD74	CD74HC126				
	THERMAL METRIC ⁽¹⁾	N (PDIP)	D (SOIC)	UNIT			
		14 PINS	14 PINS				
R _{θJA}	Junction-to-ambient thermal resistance	62.2	133.6	°C/W			
R _{0JC(top)}	Junction-to-case (top) thermal resistance	50.0	89.0	°C/W			
$R_{\theta JB}$	Junction-to-board thermal resistance	42.0	89.5	°C/W			
Ψ_{JT}	Junction-to-top characterization parameter	29.6	45.5	°C/W			
Ψ_{JB}	Junction-to-board characterization parameter	41.7	89.1	°C/W			
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W			

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application

6.5 Electrical Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

		niee-all temperature range, typical va		Operating free-air temperature (T _A)												
PARAMETER TEST COND		TEST CONDITIONS V _C		V _{CC}		25°C -40°C to 85°C			°C	-55°C to 125°C			UNIT			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX			
					2 V	1.9			1.9			1.9				
			I _{OH} = –20 μΑ	4.5 V	4.4			4.4			4.4					
.,	High-level	V _I = V _{IH} or		6 V	5.9			5.9			5.9			.,		
V _{OH}	output voltage	V _{IL}	I _{OH} = -6 mA	4.5 V	3.98			3.84			3.7			V		
			I _{OH} = -7.8 mA	6 V	5.48			5.34			5.2					
		level output $V_I = V_{IH}$ or ge				2 V			0.1			0.1			0.1	
			I _{OL} = 20 μΑ	4.5 V			0.1			0.1			0.1			
V _{OL}			F	6 V			0.1			0.1			0.1	v		
- OL			I _{OL} = 6 mA	4.5 V			0.26			0.33			0.4			
				I _{OL} = 7.8 mA	6 V			0.26			0.33			0.4		
I	Input leakage current	V _I = V _{CC} or		6 V			±0.1			±1			±1	μA		
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V			8			80			160	μA		
I _{OZ}	Three-state leakage current	V _I = V _{IH} or V _{IL}		6 V			±0.5			±5			±10	μА		
Ci	Input capacitance			5 V			10			10			10	pF		
Co	Three-state output capacitance						20			20			20	pF		



6.6 Switching Characteristics

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

				TEST		Operat	ing free-air tempera	ture (T _A)					
	PARAMETER	FROM	то	CONDITIO	V _{cc}	25°C	-40°C to 85°C	-55°C to 125°C	UNIT				
				NS		MIN TYP MAX	MIN TYP MAX	MIN TYP MAX					
					2 V	100	125	150					
	Dranagation dalay	Α	Υ	C _L = 50 pF	4.5 V	20	25	30					
t _{pd}	Propagation delay				6 V	17	7 21	36	ns				
		Α	Υ	C _L = 15 pF	5 V	8			1				
	Enable delay					2 V	125	155	190				
		able delay	DE Y	C _L = 50 pF	4.5 V	25	31	38					
t _{en}					6 V	2.	1 26	32	ns				
		OE	Υ	C _L = 15 pF	5 V	10			1				
				Y		2 V	125	155	190				
	Disable dales	OE	Y		Υ	C _L = 50 pF	4.5 V	25	31	38			
t _{dis}	Disable delay				6 V	2	1 26	32	ns				
		OE	Υ	C _L = 15 pF	5 V	10			1				
					2 V	60	75	90					
t _t	Transition-time	ansition-time	Y C _L	C _L = 50 pF	4.5 V	12	2 15	18	ns				
						6 V	10	13	15	1			

6.7 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	<u> </u>	3 , 11		- 1		
	PARAMETER	TEST CONDITIONS	V _{cc}	MIN	TYP MA	AX UNIT
C_{pd}	Power dissipation capacitance per gate	No load	5 V		30	pF

6.8 Typical Characteristics

 $T_A = 25^{\circ}C$

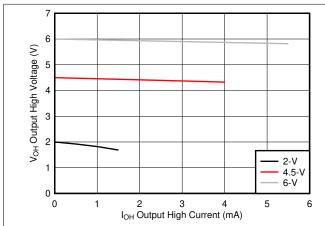


Figure 6-1. Typical output voltage in the high state (V_{OH})

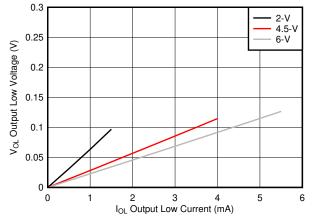
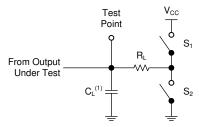


Figure 6-2. Typical output voltage in the low state (V_{OL})



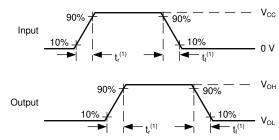
7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.
- The outputs are measured one at a time, with one input transition per measurement.



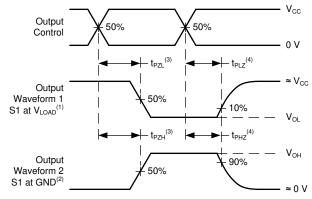
A. C_L = 50 pF and includes probe and jig capacitance.

Figure 7-1. Load Circuit



A. t_t is the greater of t_r and t_f.

Figure 7-2. Voltage Waveforms Transition Times



A. The maximum between t_{PLH} and t_{PHL} is used for t_{pd}.

Figure 7-3. Voltage Waveforms Propagation Delays

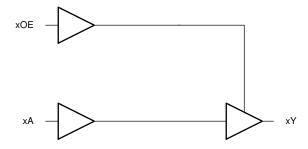


8 Detailed Description

8.1 Overview

This device contains four independent buffers with 3-state outputs. Each gate performs the Boolean function Y = A in positive logic.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS 3-State Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to over-current. The electrical and thermal limits defined in the *Section 6.1* must be followed at all times.

The CD74HC126 can drive a load with a total capacitance less than or equal to the maximum load listed in the Section 6.6 connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the Section 6.1.

3-State outputs can be placed into a high-impedance state. In this state, the output will neither source nor sink current, and leakage current is defined by the I_{OZ} specification in the *Section 6.5*. A pull-up or pull-down resistor can be used to ensure that the output remains HIGH or LOW, respectively, during the high-impedance state.

8.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the Section 6.5. The worst case resistance is calculated with the maximum input voltage, given in the Section 6.1, and the maximum input leakage current, given in the Section 6.5, using ohm's law ($R = V \div I$).

Signals applied to the inputs need to have fast edge rates, as defined by the input transition time in the *Section* 6.3 to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.



8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Figure 8-1.

CAUTION

Voltages beyond the values specified in the Section 6.1 table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

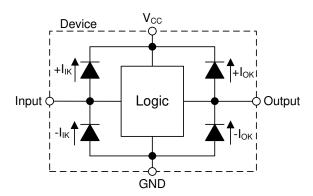


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1. Function Table

INP	OUTPUT				
OE	OE A				
L	X	Z			
Н	L	L			
Н	Н	Н			

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

In this application, a 3-state buffer is used to enable or disable a data connection as shown in *Figure 9-1*. It is common to see all four channels of a device used together for controlling a 4-bit data bus, however each channel of the device can be used independently. Unused channels should have the inputs terminated at ground or V_{CC} and the output left unconnected.

When the output of the device is active, the data signal will be replicated at the output. When the output of the device is disabled, the output will be in a high-impedance state, and the output voltage will be determined by the circuit connected to the output pin. This circuit is most commonly used when a bus must be completely disabled. One example of this situation is when the circuitry connected to the output is to be powered off for an extended period of time to save system power, and the inputs to that circuitry cannot have a voltage present due to protective clamp diodes.

9.2 Typical Application

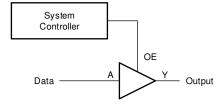


Figure 9-1. Typical application schematic

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the Section 6.3. The supply voltage sets the device's electrical characteristics as described in the Section 6.5.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the CD74HC126 plus the maximum supply current, I_{CC} , listed in the *Section 6.5*. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the *Section 6.1*.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.

CAUTION

The maximum junction temperature, T_J(max) listed in the Section 6.1, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Section 6.1. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the CD74HC126, as specified in the *Section 6.5*, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The CD74HC126 has standard CMOS inputs, so input signal edge rates cannot be slow. Slow input edge rates can cause oscillations and damaging shoot-through current. The recommended rates are defined in the *Section* 6.3.

Refer to the Section 8.3 for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Section 6.5*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Section 6.5*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Section 8.3 for additional information regarding the outputs for this device.

9.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the Section 11.
- 2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the CD74HC126 to the receiving device.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_O(max)) \Omega$. This will ensure that the maximum output current from the *Section 6.1* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.
- 4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

9.2.3 Application Curves

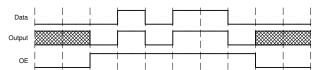


Figure 9-2. Typical application timing diagram



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Section 6.3*. Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Figure 11-1*.



11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

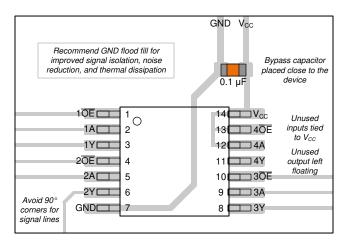


Figure 11-1. Example layout for the CD74HC126



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- · Designing with Logic

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.3 Trademarks

TI E2E™ is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status	Material type	Package Pins	Package qty Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
CD54HC126F3A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8684801CA CD54HC126F3A
CD54HC126F3A.A	Active	Production	CDIP (J) 14	25 TUBE	No	SNPB	N/A for Pkg Type	-55 to 125	5962-8684801CA CD54HC126F3A
CD74HC126E	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC126E
CD74HC126E.A	Active	Production	PDIP (N) 14	25 TUBE	Yes	NIPDAU	N/A for Pkg Type	-55 to 125	CD74HC126E
CD74HC126M	Obsolete	Production	SOIC (D) 14	-	-	Call TI	Call TI	-55 to 125	HC126M
CD74HC126M96	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU SN	Level-1-260C-UNLIM	-55 to 125	HC126M
CD74HC126M96.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 125	HC126M

⁽¹⁾ Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

⁽²⁾ Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

⁽⁴⁾ Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

PACKAGE OPTION ADDENDUM

www.ti.com 9-Nov-2025

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF CD54HC126, CD74HC126:

Military : CD54HC126

NOTE: Qualified Version Definitions:

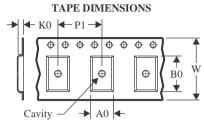
- Catalog TI's standard catalog product
- Military QML certified for Military and Defense Applications

PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

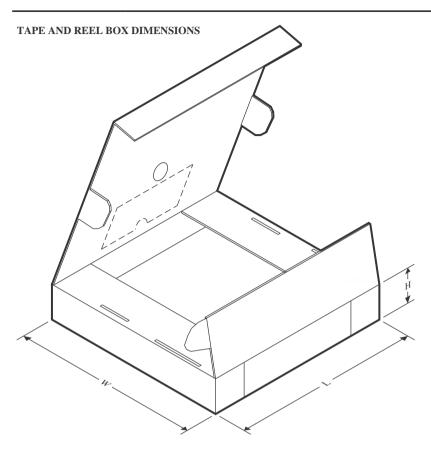
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CD74HC126M96	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
CD74HC126M96	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

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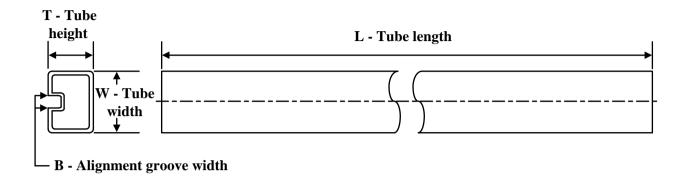
*All dimensions are nominal

Device	Device Package Type		Pins SPQ		Length (mm)	Width (mm)	Height (mm)	
CD74HC126M96	SOIC	D	14	2500	366.0	364.0	50.0	
CD74HC126M96	SOIC	D	14	2500	353.0	353.0	32.0	

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CD74HC126E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC126E	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC126E.A	N	PDIP	14	25	506	13.97	11230	4.32
CD74HC126E.A	N	PDIP	14	25	506	13.97	11230	4.32



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm, per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
- 5. Reference JEDEC registration MS-012, variation AB.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT

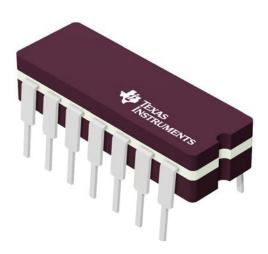


NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



CERAMIC DUAL IN LINE PACKAGE



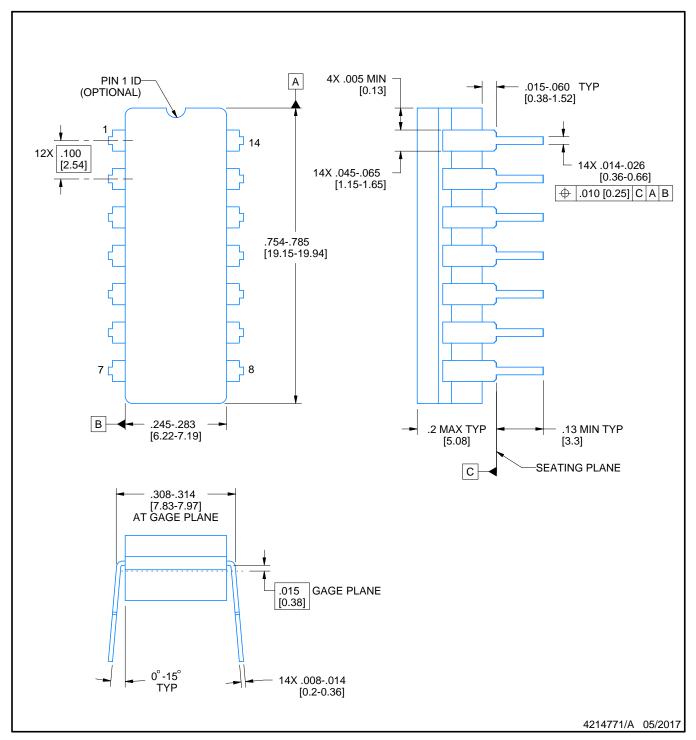
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





CERAMIC DUAL IN LINE PACKAGE

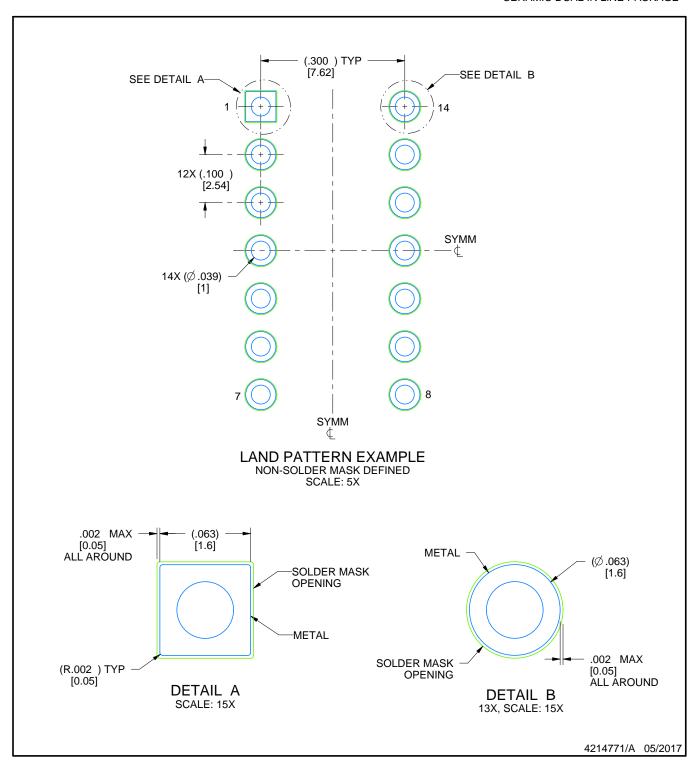


NOTES:

- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



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